IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A packaging device for packaging electronic circuit units ~~(102)~~, comprising:
   a) a packaging means ~~(100)~~, which surrounds the electronic circuit unit ~~(102)~~ and which is electrically insulating; and
   b) particles dispersed in the packaging means ~~(100)~~, said particles having a high thermal conductivity, ~~characterized in that~~ wherein
   c) the particles dispersed in the packaging means ~~(100)~~ are formed as nanoelements ~~(101)~~.
2. (Currently Amended) The device as claimed in claim 1, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as nanotubes.
3. (Currently Amended) The device as claimed in claim 1, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as silicon nanowires.
4. (Currently Amended) The device as claimed in claim 2, ~~characterized in that~~ wherein the nanotubes are essentially constructed from carbon and formed as carbon nanotubes ~~(CNT)~~.
5. (Currently Amended) The device as claimed in ~~one of the preceding claims, characterized in that~~ claim 1, wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided with an electrically insulating sheathing layer ~~(106)~~.
6. (Currently Amended) The device as claimed in ~~one of claims 1 to 4, characterized in that~~ claim 1, wherein the nanoelements ~~(101)~~ forming the dispersed particles are functionalized in such a way that electrical conduction properties of the nanoelements ~~(101)~~ are suppressed.
7. (Currently Amended) The device as claimed in ~~one of claims 1 to 4, characterized in that~~ claim 1, wherein the nanoelements ~~(101)~~ forming the dispersed particles are intrinsically doped in such a way that a metallic Π system is eliminated.

8. (Currently Amended) The device as claimed in claim 7, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as carbon nanotubes ~~(CNT)~~ and are intrinsically doped with nitrogen ~~(N)~~ and/or with boron ~~(B)~~ in such a way that the metallic Π system is eliminated.

9. (Currently Amended) The device as claimed in ~~one of claims 1 to 4, characterized in that~~ claim 1, wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as hetero-nanotubes having a large band gap.

10. (Currently Amended) The device as claimed in claim 9, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as hetero-nanotubes containing boron nitride ~~(BN)~~, boron-carbon nitride ~~(BCN)~~ and/or vanadium pentoxide ~~(V_2O_5)~~.

11. (Currently Amended) The device as claimed in ~~one of the preceding claims, characterized in that~~ claim 1, wherein the nanoelements ~~(101)~~ forming the dispersed particles are oriented with a longitudinal axis parallel to at least one heat flow which flows between the circuit unit ~~(102)~~ and an outer side of the packaging device.

12. (Currently Amended) The device as claimed in ~~one of the preceding claims, characterized in that~~ claim 1, wherein the nanoelements ~~(101)~~ forming the dispersed particles have in their longitudinal axes extents which are significantly smaller than a thickness of the packaging means.

13. (Currently Amended) The device as claimed in claim 5, ~~characterized in that~~ wherein the electrically insulating sheathing layer ~~(106)~~ surrounding the nanoelements ~~(101)~~ forming the dispersed particles has a layer thickness in a range of 20 nm to 30 nm.

14. (Currently Amended) An electrical insulator comprising a packaging device as claimed in ~~one or more of claims 1 to 13~~ claim 1.

15. (Currently Amended) A method for packaging electronic circuit units ~~(102)~~, comprising the steps of:

a) providing a packaging means ~~(100)~~, which is electrically

insulating;

b) dispersing particles having a high thermal conductivity in the packaging means ~~(100)~~; and

c) surrounding the electronic circuit unit ~~(102)~~ with the packaging means ~~(100)~~ in which the particles having the high thermal conductivity are dispersed, ~~characterized in that~~ wherein

d) dispersing the particles ~~dispersed~~ in the packaging means ~~(100)~~ are provided as nanoelements ~~(101)~~.

16. (Currently Amended) The method as claimed in claim 15, ~~characterized in that~~ wherein after surrounding the electronic circuit unit ~~(102)~~ with the packaging means ~~(100)~~ in which the particles having the high thermal conductivity are dispersed, the packaging means is cured.

17. (Currently Amended) The method as claimed in claim 15, ~~characterized in that~~ wherein a heat flow is transported from the circuit unit ~~(102)~~ to an outer side of the packaging device via the packaging means ~~(100)~~ in which the particles having the high thermal conductivity are dispersed, in order to cool the circuit unit ~~(102)~~.

18. (Currently Amended) The method as claimed in claim 15, ~~characterized in that~~ wherein a heat flow is transported from an outer side of the packaging device to the circuit unit ~~(102)~~ via the packaging means ~~(100)~~ in which the particles having the high thermal conductivity are dispersed, in order to heat the circuit unit ~~(102)~~.

19. (Currently Amended) The method as claimed in claim 15, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as nanotubes.

20. (Currently Amended) The method as claimed in claim 15, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as silicon nanowires.

21. (Currently Amended) The method as claimed in claim 15, characterized in that the nanotubes are essentially produced from carbon in the form of carbon nanotubes ~~(CNT)~~.

22. (Currently Amended) The method as claimed in ~~one of claims 15 and 19 to 21, characterized in that~~ claim 15, wherein the nanoelements ~~(101)~~ forming the dispersed particles are coated with an electrically

insulating sheathing layer ~~(106)~~.

23. (Currently Amended) The method as claimed in ~~one of claims 15 and 19 to 21, characterized in that~~ claim 15, wherein the nanoelements ~~(101)~~ forming the dispersed particles are functionalized in such a way that electrical conduction properties of the nanoelements ~~(101)~~ are suppressed.

24. (Currently Amended) The method as claimed in ~~one of claims 15 and 19 to 21, characterized in that~~ claim 15, wherein the nanoelements ~~(101)~~ forming the dispersed particles are intrinsically doped in such a way that a metallic Π system is eliminated.

25. (Currently Amended) The method as claimed in claim 24, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as carbon nanotubes ~~(CNT)~~ and are intrinsically doped with nitrogen ~~(N)~~ and/or with boron ~~(B)~~ in such a way that the metallic Π system is eliminated.

26. (Currently Amended) The method as claimed in ~~one of claims 15 and 19 to 21, characterized in that~~ claim 15, wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as hetero-nanotubes having a large band gap.

27. (Currently Amended) The method as claimed in claim 26, ~~characterized in that~~ wherein the nanoelements ~~(101)~~ forming the dispersed particles are provided as hetero-nanotubes containing boron nitride ~~(BN)~~, boron-carbon nitride ~~(BCN)~~ and/or vanadium pentoxide ~~(V_2O_5)~~.

28. (Currently Amended) The method as claimed in ~~one of claims 15 to 27, characterized in that~~ claim 15, wherein the nanoelements ~~(101)~~ forming the dispersed particles are oriented with a longitudinal axis parallel to at least one heat flow which flows between the circuit unit ~~(102)~~ and an outer side of the packaging device.

29. (Currently Amended) The method as claimed in ~~one of claims 15 to 28, characterized in that~~ claim 15, wherein the nanoelements ~~(101)~~ forming the dispersed particles have in their longitudinal axes extents which are significantly smaller than a thickness of the packaging means.